



40V N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD18504Q5A

FEATURES

- Ultra Low Qg and Qgd
- **Low Thermal Resistance**
- **Avalanche Rated**
- Logic Level
- Pb Free Terminal Plating
- **RoHS Compliant**
- **Halogen Free**
- SON 5-mm × 6-mm Plastic Package

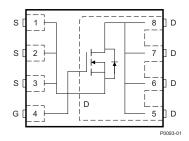
APPLICATIONS

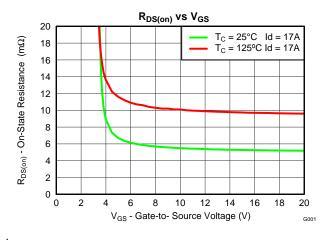
- **DC-DC Conversion**
- Secondary Side Synchronous Rectifier
- **Battery Motor Control**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

Figure 1. Top View





PRODUCT SUMMARY

	/alues at 25°C therwise stated	TYPICAL VA	UNIT	
V_{DS}	Drain to Source Voltage	40		٧
Q_g	Gate Charge Total (4.5V)	7.7	nC	
Q_{gd}	Gate Charge Gate to Drain	to Drain 2.4		nC
D	Drain to Source On Resistance	$V_{GS} = 4.5V$	7.5	mΩ
R _{DS(on)}	Diam to Source On Resistance	V _{GS} = 10V 5.3		mΩ
$V_{GS(th)}$	Threshold Voltage	1.9	V	

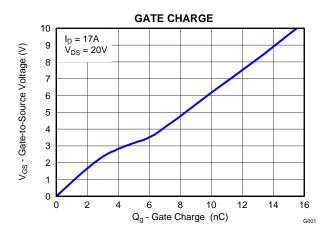
ORDERING INFORMATION

Device Package		Media	Qty	Ship
CSD18504Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V _{DS}	Drain to Source Voltage	40	V
V _{GS}	Gate to Source Voltage	±20	V
	Continuous Drain Current (Package limited), T _C = 25°C	50	
I_D	Continuous Drain Current (Silicon limited), T _C = 25°C	75	Α
	Continuous Drain Current, T _A = 25°C ⁽¹⁾	15	
I_{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	95	Α
P _D	Power Dissipation ⁽¹⁾	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 43A$, $L = 0.1 mH$, $R_G = 25\Omega$	92	mJ

- (1) Typical $R_{\theta,JA} = 40^{\circ}\text{C/W}$ on a 1-inch², 2-oz. Cu pad on a 0.06inch thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics		·			
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	40			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 32V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = 20V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5	1.9	2.4	V
Р	Drain to Course On Registeres	V _{GS} = 4.5V, I _D = 17A		7.5	9.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V, I _D = 17A		5.3	6.6	mΩ
9 _{fs}	Transconductance	V _{DS} = 20V, I _D = 17A		71		S
Dynamic	: Characteristics					
C _{iss}	Input Capacitance			1380	1656	pF
C _{oss}	Output Capacitance	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz		310	372	pF
C _{rss}	Reverse Transfer Capacitance			8	9.6	pF
R_G	Series Gate Resistance			1.4	2.8	Ω
Qg	Gate Charge Total (4.5V)			7.7	9.2	nC
Qg	Gate Charge Total (10V)			16	19	
Q _{gd}	Gate Charge Gate to Drain	$V_{DS} = 20V, I_D = 17A$		2.4		nC
Q _{gs}	Gate Charge Gate to Source			3.2		nC
$Q_{g(th)}$	Gate Charge at Vth			2.2		nC
Q _{oss}	Output Charge	V _{DS} = 20V, V _{GS} = 0V		21		nC
t _{d(on)}	Turn On Delay Time			3.2		ns
t _r	Rise Time	$V_{DS} = 20V, V_{GS} = 10V,$		6.8		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 17A, R_G = 0$		12		ns
t _f	Fall Time			2		ns
Diode Cl	haracteristics					
V _{SD}	Diode Forward Voltage	I _{SD} = 17A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DS} = 20V, I _F = 17A,		39		nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/μs		28		ns

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

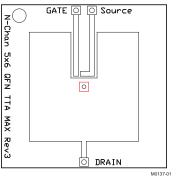
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			2	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1)(2)			50	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

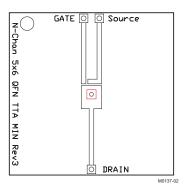
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Max $R_{\theta JA} = 50^{\circ}C/W$ when mounted on 1 inch2 (6.45 cm2) of 2oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 125$ °C/W when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

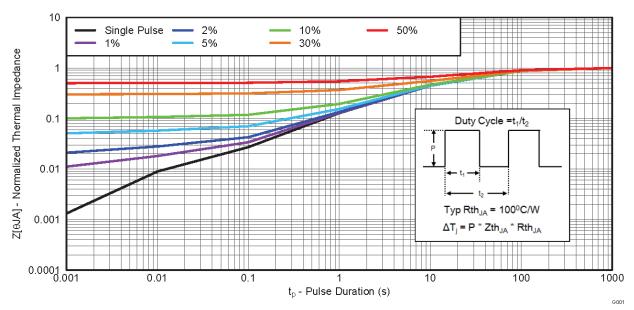
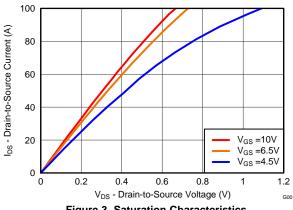


Figure 2. Transient Thermal Impedance





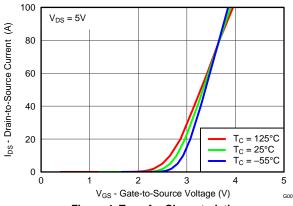


Figure 4. Transfer Characteristics

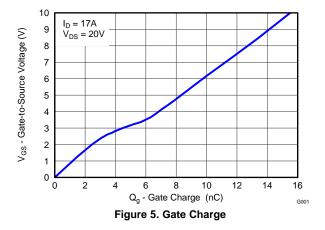
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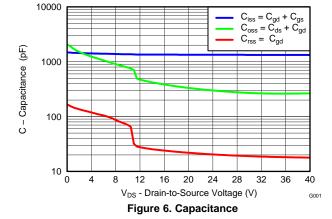
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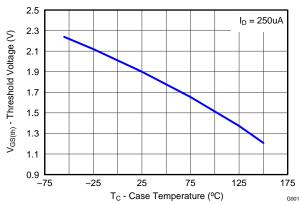
TYPICAL MOSFET CHARACTERISTICS (continued)

Product Folder Links: CSD18504Q5A

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$







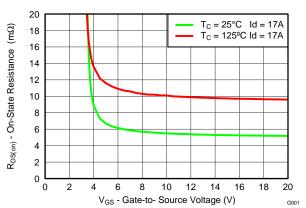
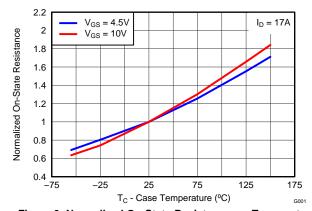


Figure 7. Threshold Voltage vs. Temperature

Figure 8. On-State Resistance vs. Gate-to-Source Voltage



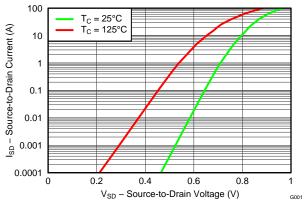


Figure 9. Normalized On-State Resistance vs. Temperature

Figure 10. Typical Diode Forward Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

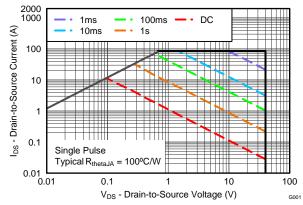


Figure 11. Maximum Safe Operating Area

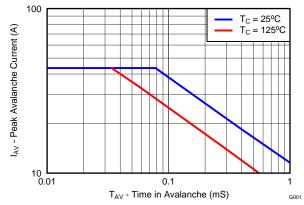


Figure 12. Single Pulse Unclamped Inductive Switching

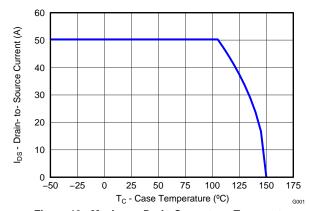


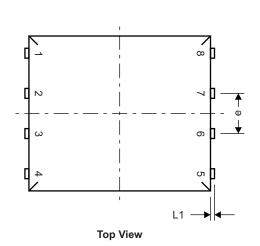
Figure 13. Maximum Drain Current vs. Temperature

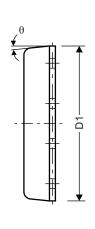
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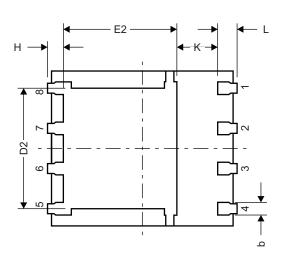


MECHANICAL DATA

Q5A Package Dimensions







Front View

Side View

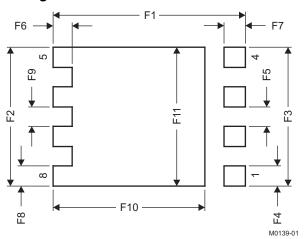
Bottom View

M0135-01

DIM	MILLIMETERS							
DIM	MIN	NOM	MAX					
А	0.90	1.00	1.10					
b	0.33	0.41	0.51					
С	0.20	0.25	0.34					
D1	4.80	4.90	5.00					
D2	3.61	3.81	4.02					
Е	5.90	6.00	6.10					
E1	5.70	5.75	5.80					
E2	3.38	3.58	3.78					
е	1.17	1.27	1.37					
Н	0.41	0.56	0.71					
K	1.10							
L	0.51	0.61	0.71					
L1	0.06	0.13	0.20					
θ	0°		12°					



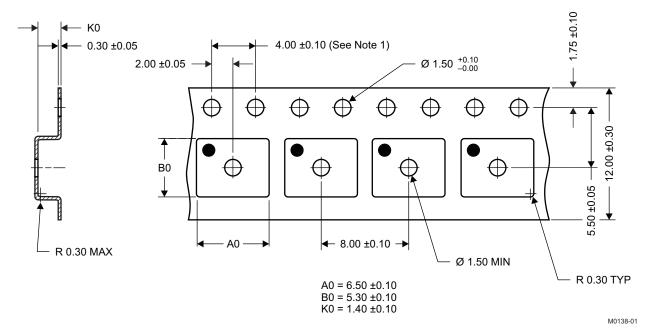
Figure 14. Recommended PCB Pattern



DIM	MILLIN	IETERS	INC	HES
DIN	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5A Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

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REVISION HISTORY

Changes from Original (June 2012) to Revision A	Page
Changed the Transconductance TYP value From: 63 S To: 71 S	2
• Changed the Turn On and Turn Off Delay Time, Rise and Fall Time Test Conditions From: I_{DS} = 17A, R_{G} = 2 Ω To: I_{DS} = 17, R_{G} = 0 Ω	2
Changed the Q _{rr} Reverse Recovery Charge TYP value From: 18 nC To: 39 nC	2
Changes from Revision A (October 2012) to Revision B	Page
Changed the R _{DS(on)} vs V _{GS} and Gate Charger graphs	1
OL 15 M 1 5 54 T 5000M	
Changed R _{BJA} Max value From: 51 To: 50°C/W	





6-Nov-2012

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Samples
	(1)		Drawing			(2)		(3)	(Requires Login)
CSD18504Q5A	ACTIVE	SON	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

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(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18504Q5A	SON	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	kage Type Package Drawing Pins SPC				Width (mm)	Height (mm)
CSD18504Q5A	SON	DQJ	8	2500	340.0	340.0	38.0

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